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(54) **MANUFACTURING METHOD OF A SEMICONDUCTOR DEVICE COMPRISING A SCHOTTKY DIODE AND A HIGH ELECTRON MOBILITY TRANSISTOR**

HERSTELLUNGSVERFAHREN FÜR EINE HALBLEITERVORRICHTUNG MIT EINER
SCHOTTKY-DIODE UND EINEM TRANSISTOR MIT HOHER ELEKTRONENMOBILITÄT

PROCÉDÉ DE FABRICATION D'UN DISPOSITIF SEMI-CONDUCTEUR COMPRENANT UNE DIODE
SCHOTTKY ET UN TRANSISTOR À HAUTE MOBILITÉ D'ÉLECTRONS

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